



DONGGUAN NANJING ELECTRONICS LTD.,

TO-92 Plastic-Encapsulate Transistors

M8550 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

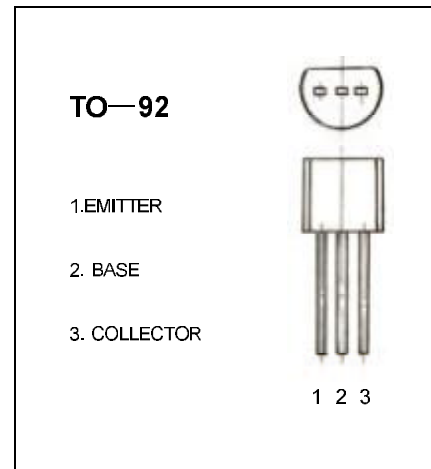
$$I_{CM} : -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu\text{A}, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C = -0.1\text{mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu\text{A}, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -5\text{mA}$	45		
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	85	300	
	$h_{FE(3)}$	$V_{CE} = -1\text{V}, I_C = -800\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f = 30\text{MHz}$	150		MHz

* Pulse Test : pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.